

NCEP0160F

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP0160F uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

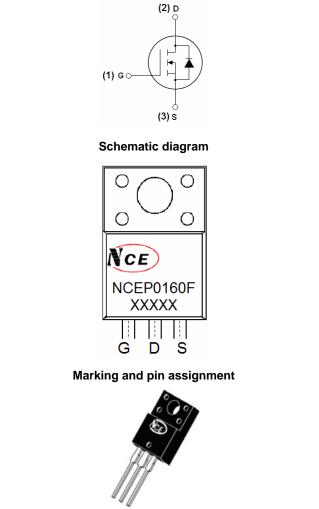
- V_{DS} =100V,I_D =60A
 - $R_{DS(ON)}$ =9.2m Ω (typical) @ V_{GS}=10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

100% ΔVds TESTED!



TO-220F top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP0160F	NCEP0160F	TO-220F	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	100	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	Ι _D	60	A
Drain Current-Continuous(T _C =100 ℃)	I _D (100℃)	42.4	А
Pulsed Drain Current	I _{DM}	240	А
Maximum Power Dissipation	PD	35	W
Derating factor		0.23	W/°C
Single pulse avalanche energy ^(Note 5)	E _{AS}	290	mJ
Operating Junction and Storage Temperature Range	TJ,TSTG	-55 To 175	°C





Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	4.3	°C /W
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Electrical Characteristics (Tc=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	I		•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	IV,V _{GS} =0V -		1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V -		-	±100	nA
On Characteristics (Note 3)	I					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, I _D =250µA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	9.2	10.8	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =30A	-	40	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss		-	2500	-	PF
Output Capacitance	C _{oss}	V _{DS} =50V,V _{GS} =0V, F=1.0MHz	-	273	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHZ	-	27	-	PF
Switching Characteristics (Note 4)	I		•			
Turn-on Delay Time	t _{d(on)}		-	13	-	nS
Turn-on Rise Time	tr	V_{DD} =50V,I _D =30A	-	8.5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =4.7 Ω	_	29	-	nS
Turn-Off Fall Time	t _f		_	4	-	nS
Total Gate Charge	Qg	V/ F0V/1 00A	-	37		nC
Gate-Source Charge	Q _{gs}	V_{DS} =50V,I _D =30A,	_	14		nC
Gate-Drain Charge	Q _{gd}	V _{GS} =10V	_	8		nC
Drain-Source Diode Characteristics	· ·					
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =60A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	60	Α
Reverse Recovery Time	trr	T_J = 25°C, I_F = I_S	-	58		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	149		nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25 $^\circ\!\mathrm{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω

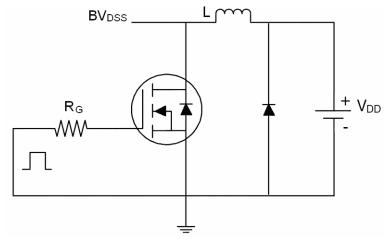


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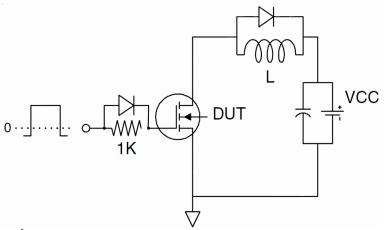
Pb Free Product



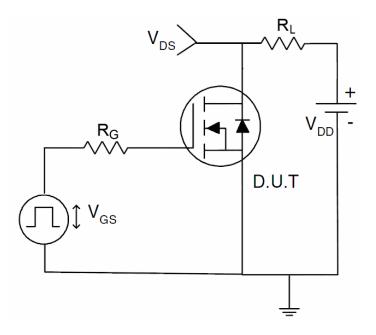
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit

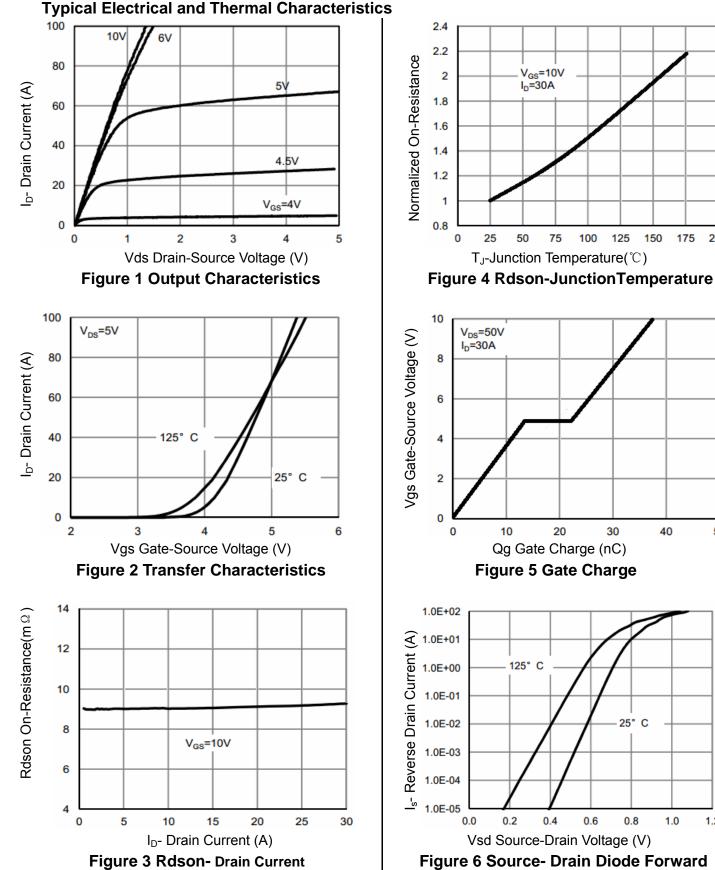


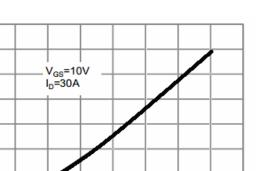


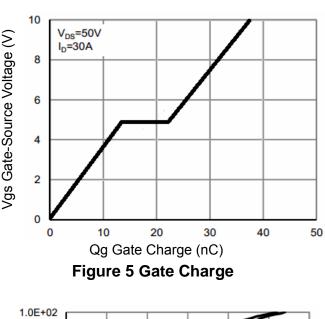
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75

100

125

150

175

200

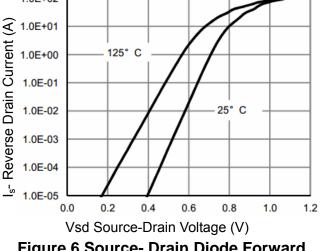
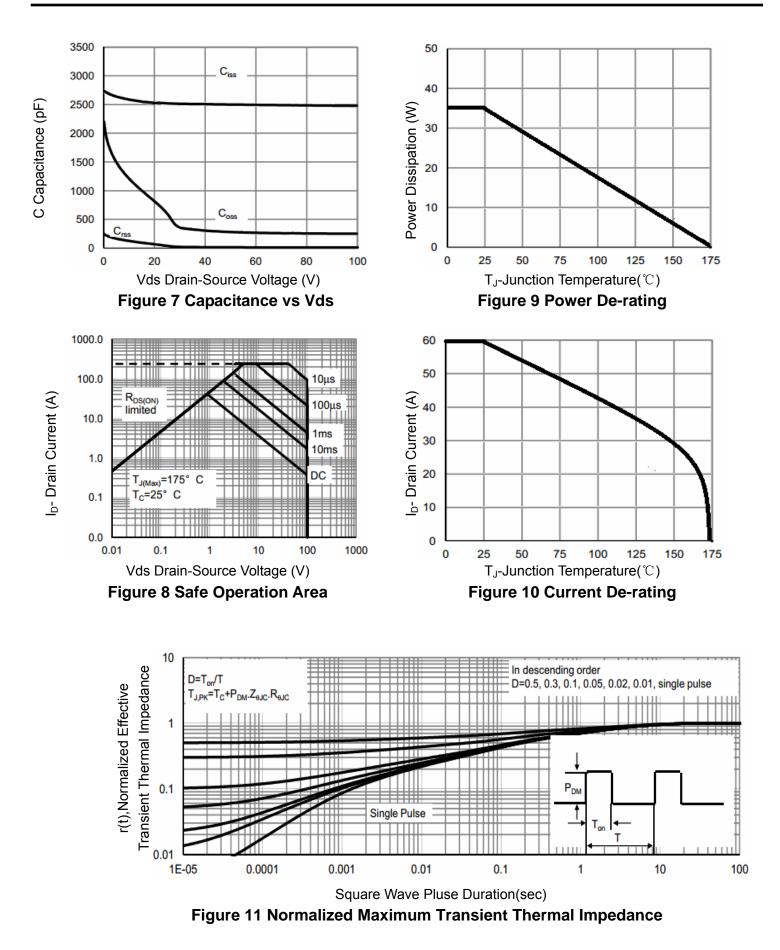


Figure 6 Source- Drain Diode Forward



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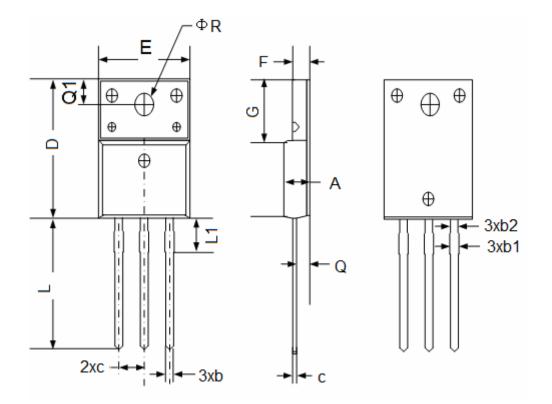


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TO-220F Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches				
Symbol	Min.	Max.	Min.	Max.			
A	4.50	4.83	0.18	0.19			
b	0.70	0.91	0.03	0.04			
b1	1.20	1.47	0.05	0.06			
b2	1.10	1.38	0.04	0.05			
с	0.45	0.63	0.02	0.02			
D	15.67	16.07	0.62	0.63			
е	2.54	2.54 BSC		0.10 BSC			
E	9.96	10.36	0.39	0.41			
F	2.34	2.74	0.09	0.11			
G	6.48	6.90	0.26	0.27			
L	12.68	13.30	0.50	0.52			
L1	3.13	3.50	0.12	0.14			
Q	2.56	2.93	0.10	0.12			
Q1	3.20	3.40	0.13	0.13			
ΦR	3.08	3.28	0.12	0.13			







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